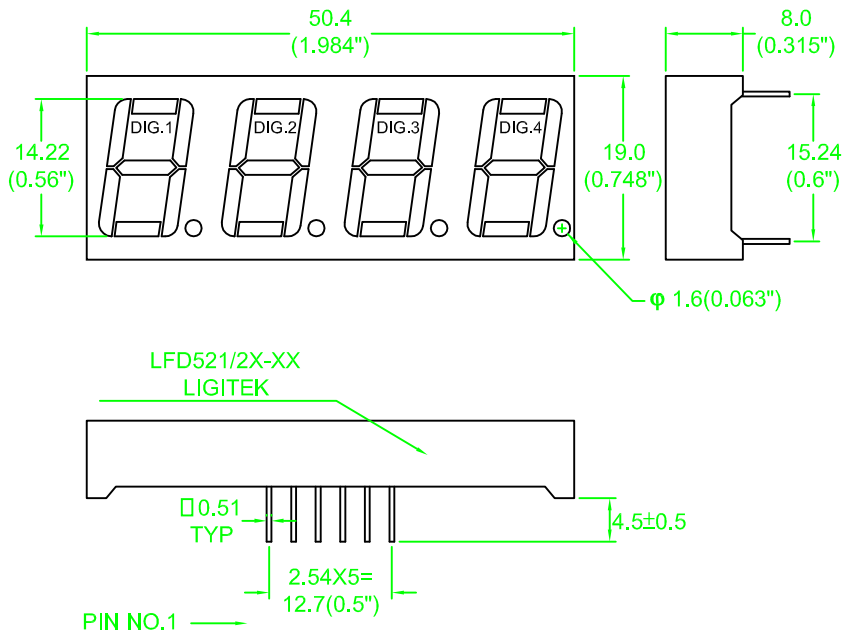
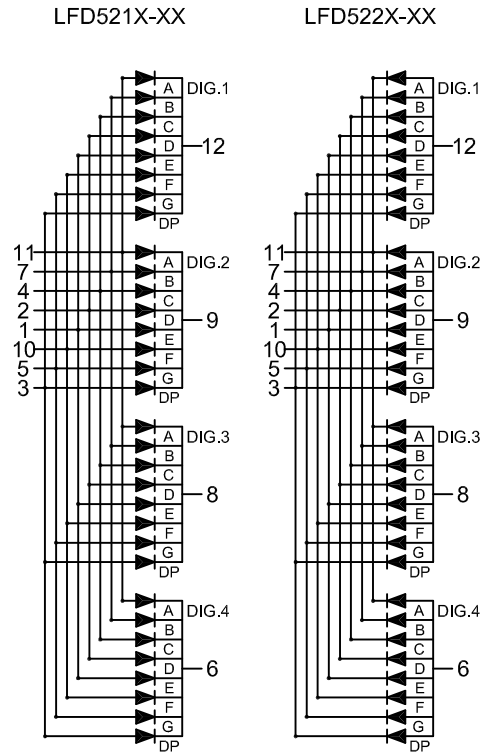


PACKAGE DIMENSION



INTERNAL CIRCUIT DIAGRAM



NOTE:1.All Dimension Are In Millimeters And (Inch)
Tolerance Is $\pm 0.25(0.01)$ " unless Otherwise Noted
2.Specifications are subject to change without notice.

▪ Connection To Electrical Schematic

Electrical connection

PIN NO	LFD521X-XX	PIN NO	LFD522X-XX
1	Anode E	1	Cathode E
2	Anode D	2	Cathode D
3	Anode DP	3	Cathode DP
4	Anode C	4	Cathode C
5	Anode G	5	Cathode G
6	Common Cathode Dig.4	6	Common Anode Dig.4
7	Anode B	7	Cathode B
8	Common Cathode Dig.3	8	Common Anode Dig.3
9	Common Cathode Dig.2	9	Common Anode Dig.2
10	Anode F	10	Cathode F
11	Anode A	11	Cathode A
12	Common Cathode Dig.1	12	Common Anode Dig.1

• Part Selection And Application Information(Ratings At 25°C Ambient)

PART NO	CHIP		common cathode or anode	λ_p (nm)	$\Delta\lambda$ (nm)	Electrial					IV-M
	material	emitted				Vf(v)			Iv(mcd)		
						Min	Typ	Max	Min	Typ	
LFD5216-XX	GaAlAs	Red	Common Cathode	660	20	1.5	1.7	2.4	7.2	12	2:1
LFD5215-XX	GaAlAs	Red		660	20	1.5	1.7	2.4	4.0	6.0	2:1
LFD5211-XX	GaP	Red		697	90	1.7	2.1	2.8	0.5	1.0	2:1
LFD5212-XX	GaP	Green		565	30	1.7	2.1	2.8	1.75	2.8	2:1
LFD5213-XX	GaAsP/GaP	Yellow		585	35	1.7	2.0	2.8	1.35	2.6	2:1
LFD5214-XX	GaAsP/GaP	Orange		635	45	1.7	2.0	2.8	2.35	4.0	2:1
LFD5226-XX	GaAlAs	Red	Common Anode	660	20	1.5	1.7	2.4	7.2	12	2:1
LFD5225-XX	GaAlAs	Red		660	20	1.5	1.7	2.4	4.0	6.0	2:1
LFD5221-XX	GaP	Red		697	90	1.7	2.1	2.8	0.5	1.0	2:1
LFD5222-XX	GaP	Green		565	30	1.7	2.1	2.8	1.75	2.8	2:1
LFD5223-XX	GaAsP/GaP	Yellow		585	35	1.7	2.0	2.8	1.35	2.6	2:1
LFD5224-XX	GaAsP/GaP	Orange		635	45	1.7	2.0	2.8	2.35	4.0	2:1

▪ Absolut Maximum Rating (Ta=25°C)

Parameter	Red			Green		Yellow		Orange		Unit	Remark
	SR	HR	H		G		Y		E		
Forward Current Per Chip	40	40	15		30		20		30	mA	
Peak Current Per Chip (Duty 1/10,0.1ms Pulse Width)	200	200	60		120		80		120	mA	
Power Dissipation Per Chip	110		45	100		85		100		mW	
Derating Linear From 25°C Per Chip	0.45		0.25	0.45		0.45		0.45		mA/°C	
Reverse Current Per Any Chip	10			10		10		10		μA	
Operating Temperature	-25°C TO +85°C										
Storage Temperature	-25°C TO +85°C										

Solder Temperature 1-16 Inch Below Seating Plane For 3 Seconds At 260 °C

▪ Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=10mA
Peak Emission Wavelength	λ_p	nm	If=20mA
Spectral Line Half-Width	$\Delta\lambda$	nm	If=20mA
Reverse Current Any Chip	Ir	μA	Vr=5V
Luminous Intensity Matching Ratio	IV-M		